



K. Memory (Design & Process Technology) 분과

2021년 1월 29일(금), 14:45-16:15 / 채널 D

[FD4-K] Emerging Memory III

좌장: 민경식 교수 (국민대학교), 정연주 박사 (KIST)

<p>FD4-K-1 14:45-15:00</p>	<p>28nm Highly Reliable Embedded Flash Memory Logic Process for Automotive Grade-1 (-40~150°C) Application</p> <p>GaYoung Lee, DongHyun Kim, JongSung Woo, KyongSik Yeom, YongSeok Chung, MinJi Seo, Youngcheon Jeong, Changmin Jeon, SangJin Lee, and YongKyu Lee <i>Foundry Business, Samsung Electronics Co., Ltd.</i></p>
<p>FD4-K-2 15:00-15:15</p>	<p>Simulations of PCM's ISPP Characteristics by Comparing Different Materials and Cell Architectures</p> <p>Hwanwook Lee, Ho Thi Thu Trang, and Yongwoo Kwon <i>Material Science and Engineering, Hongik University</i></p>
<p>FD4-K-3 15:15-15:30</p>	<p>Effect of the ALD Temperature on Switching Characteristic in Cu-based CBRAM with the Solid Electrolyte of Al₂O₃</p> <p>Inseok Chae, Jun Tae Jang, Shinyoung Park, Woo Sik Choi, Jong-Ho Bae, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim <i>School of Electrical Engineering, Kookmin University</i></p>
<p>FD4-K-4 15:30-15:45</p>	<p>Ensemble of Stochastic Memristive Neural Network to Mitigate Synaptic Device Non-idealities</p> <p>Hanchan Song, Hyun Soo Nam, Jae Hyun In, Gwangmin Kim, Woon Hyung Cheong, Do Hoon Kim, and Kyung Min Kim <i>Department of Materials Science and Engineering, KAIST</i></p>
<p>FD4-K-5 15:45-16:00</p>	<p>nvSRAM을 위한 자동저장회로 개발</p> <p>고운산, 정준교, 성재영, 남기령, 이가원 <i>충남대학교 전자공학과</i></p>
<p>FD4-K-6 16:00-16:15</p>	<p>A Diffusive-Memristor-Based True Random Number Generator</p> <p>Kyung Seok Woo^{1,2}, Jae Hyun Kim^{1,2}, and Cheol Seong Hwang^{1,2} ¹<i>Department of Materials Science and Engineering, Seoul National University,</i> ²<i>Inter-University Semiconductor Research Center, Seoul National University</i></p>